

P U B L I C A T I O N S L I S T

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BOOKS

Ilan Golecki, Editor

Elzbieta Kolawa and Bernard Gollomp, Co-Editors (1998)

PROCEEDING 1998 HIGH-TEMPERATURE ELECTRONIC MATERIALS, DEVICES AND SENSORS CONFERENCE

Sponsored by the Engineering Foundation, the IEEE Electron Devices Society and the IEEE Instrumentation and Measurement Society, San Diego, CA, February 1998 (IEEE Publications, Catalog No. 98EX132, ISBN 0-7803-4737-5 (softbound), ISBN 0-7803-4438-3 (microfiche)), 221 + 16 pages.

INVITED BOOK CHAPTERS

Ilan Golecki (2001)

INDUSTRIAL CARBON CHEMICAL VAPOR INFILTRATION (CVI) PROCESSES

Chapter 7 in P. Delhaès, ed., **World of Carbon, Vol. 3: Fibers and Composites**, Gordon and Breach, London (2001, in print).

INVITED REVIEW PAPERS

4. Ilan Golecki and Dave Narasimhan (2001)

NOVEL REAL-TIME METHOD FOR MEASURING THE DENSIFICATION RATE OF CARBON-CARBON FIBER-MATRIX COMPOSITES AND OTHER ARTICLES

Proc. 25th Annual Conf. on Composites, Advanced Ceramics, Materials and Structures, American Ceramic Society, Cocoa Beach, FL, January 2001, M. Singh and T. Jessen, eds., Ceramic Engineering & Science Proc. **22**, Issue No. 3, pp. 103-114 (2001).

3. I. Golecki (1997)

RAPID VAPOR-PHASE DENSIFICATION OF REFRACTORY COMPOSITES

Materials Science and Engineering: Reports, **R20**, No.2, 37-124.

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RECENT ADVANCES IN RAPID VAPOR-PHASE DENSIFICATION OF REFRACTORY COMPOSITES

Proc. Thirteenth Intl. Conf. on Chemical Vapor Deposition (CVD-XIII), The Electrochemical Society, Los Angeles, CA, May 1996, T.M. Besmann, M.D. Allendorf, McD. Robinson and R.K. Ulrich, eds., ECS Proc. Vol. 96-5, pp. 547-554.

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THE CURRENT STATUS OF SILICON-ON-SAPPHIRE AND OTHER HETEROEPITAXIAL SILICON-ON-INSULATOR TECHNOLOGIES

Proc. Symp. on the Comparison of Thin Film Transistors and SOI Technologies, Materials Research Soc. Meeting, Albuquerque, NM, February 1984 (M.W. Thompson and H.W. Lam, eds.) Vol. **33**, pp. 3-23.

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EFFECT OF OXIDATION-INDUCED WEIGHT LOSS ON MECHANICAL PROPERTIES OF TWO-DIMENSIONAL CARBON-CARBON COMPOSITES
Proc. 46th International SAMPE Symposium and Exhibition, Long Beach, CA, May 2001, Society for the Advancement of Material and Process Engineering (SAMPE), L. Repecka and F.F. Saremi, eds., pp. 678-689.
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ABSTRACTS OF INVITED ORAL CONFERENCE PRESENTATIONS

3. Ilan Golecki and Dave Narasimhan (2001)

NOVEL REAL-TIME METHOD FOR MEASURING THE DENSIFICATION RATE OF CARBON-CARBON FIBER-MATRIX COMPOSITES AND OTHER ARTICLES

25th Annual International Conf. on Advanced Ceramics & Composites, American Ceramic Society, Cocoa Beach, FL, January 2001, W. Mullins, K. Logan, Z. Munir and R. Spriggs, eds., paper # S1-007-01, p.15 in Conference Meeting Guide.

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RECENT ADVANCES IN RAPID VAPOR-PHASE DENSIFICATION OF REFRactory COMPOSITES

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THE CURRENT STATUS OF SILICON-ON-SAPPHIRE AND OTHER HETEROEPITAXIAL SILICON-ON-INSULATOR TECHNOLOGIES

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ABSTRACTS OF CONTRIBUTED ORAL CONFERENCE PRESENTATIONS

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(in French)

Thesis presented to the Faculty of Sciences, University of Neuchâtel, Physics Institute, CH-2000 Neuchâtel, Switzerland, for the degree of Docteur ès Sciences in Physics, January 1978 (207 pp., 53 figures, 7 tables). Printing authorized and degree received March 1978.

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THE DEVELOPMENT AND CALIBRATION OF AN INTERFEROMETRIC GAS ANALYSIS SYSTEM FOR THE MEASUREMENT OF CHANGES IN STOICHIOMETRY IN METAL OXIDES

(in Hebrew)

Thesis presented to the Senate of the Technion - Israel Institute of Technology, Haifa, Israel, for the degree of M.Sc. in Physics, January 1974 (103 pp., 29 figures, 4 tables). Degree received March 1974.

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